



US 20240213373A1

(19) **United States**

(12) **Patent Application Publication**
WANG et al.

(10) **Pub. No.: US 2024/0213373 A1**

(43) **Pub. Date: Jun. 27, 2024**

(54) **FIELD EFFECT TRANSISTOR AND
METHOD FOR MANUFACTURING SAME,
AND DISPLAY PANEL**

(52) **U.S. Cl.**

CPC **H01L 29/7869** (2013.01); **H01L 29/42364**
(2013.01); **H01L 29/66484** (2013.01); **H01L**
29/78645 (2013.01)

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(21) Appl. No.: **17/920,351**

(22) PCT Filed: **Nov. 26, 2021**

(86) PCT No.: **PCT/CN2021/133706**

§ 371 (c)(1),

(2) Date: **Oct. 20, 2022**

Publication Classification

(51) **Int. Cl.**

H01L 29/786 (2006.01)

H01L 29/423 (2006.01)

H01L 29/66 (2006.01)

(57)

ABSTRACT

The present disclosure provides a field effect transistor and a method for manufacturing the same, and a display panel, relating to the field of display technologies. The field effect transistor includes a substrate, an active layer, a source, a drain, a first insulating layer and an oxygenating layer. An orthographic projection of the oxygenating layer on the substrate is overlapped with an orthographic projection of a target region of the active layer on the substrate. Therefore, when the oxygenating layer is prepared, oxygen elements in the process environment can diffuse to the target region of the active layer, to oxygenate the active layer. In this way, oxygen vacancies in the active layer can be reduced, and the uniformity and stability of the active layer is improved, thereby further improving the performance of the field effect transistor.

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